



DARLINGTON COMPLEMENTARY SILICON POWER TRANSISTORS

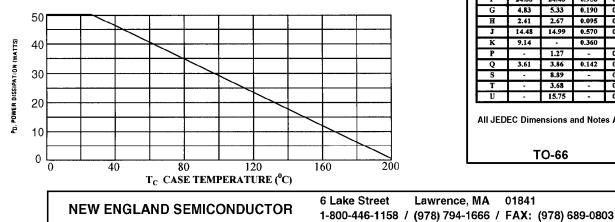
...designed for general-purpose amplifier, low-frequency switching and hammer driver applications.

- High DC Current Gain -. $h_{FE} = 3000$ (Typ) @ $I_c = 2.0$ Adc
- Low Collector-Emitter Saturation Voltage -. $V_{CE(sat)} = 2.0 \text{ Vdc} (Max) @ I_C = 2.0 \text{ Adc}$
- **Collector-Emitter Sustaining Voltage** V_{CEO(sus)} = 60 Vdc (Min) - 2N6294, 2N6296 = 80 Vdc (Min) - 2N6295, 2N6297
- Monolithic Construction with Built-In Base-Emitter Shunt Resistors

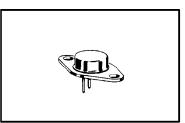
MAXIMUM RATINGS

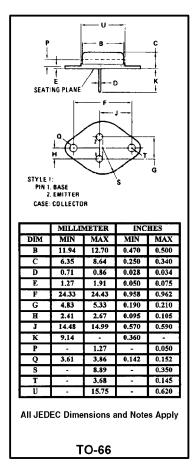
	1	2N6294	2N6295	· · · · · · · · · · · · · · · · · · ·
Rating	Symbol	2N6296	2N6297	Unit
Collector-Emitter Voltage	VCEO	60	80	Vdc
Collector-Base Voltage	V _{CB}	60) 80	
Emitter-Base Voltage	V _{EB}	5.0		Vdc
Collector Current - Continuous	I _C	4.0		Adc
- Peak		8.0		
Base Current	I _B	80		mAdc
Total Power Dissipation	P _D			
$@T_{C} = 25^{\circ}C$		50		Watts
Derate above 25°C		0.286		W/ ⁰ C
Operating and Storage Junction	T _J , T _{stg}	-65 to +200		"C
Temperature Range	, in the second s			
THERMAL CHARACTERISTIC	CS			
Characteristic		Symbol	Max	Unit
Thermal Resistance, Junction to Case		R _{g JC}	3.5	[®] C/W

FIGURE 1 -- POWER DERATING



4 AMPERE DARLINGTON COMPLEMENTARY SILICON POWER TRANSISTORS 60, 80 VOLTS **50 WATTS**





T4-4.8-860-352 REV: --

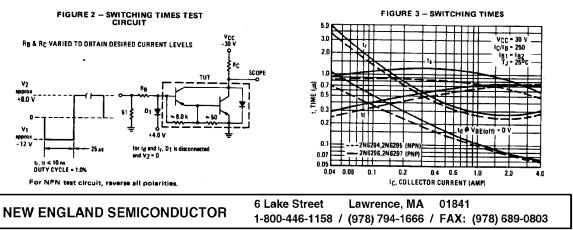
01841





Characteristics		Symbol	Min	Max	Unit
OFF CHARACTERISTICS			- -		
Collector-Emitter Sustaining Voltage	· · · · · · · · · · · · · · · · · · ·	V _{CEO(SUS)}			
$I_{\rm C} = 50 \text{ mAdc}, \ I_{\rm B} = 0$	2N6294, 2N6296	020(000)	60		Vdc
	2N6295, 2N6297		80		
Collector Cutoff Current		I _{CEO}			mAdc
$V_{CE} = 30 \text{ Vdc}, I_B = 0$	2N6294, 2N6296			0.5	
$V_{CE} = 40 \text{ Vdc}, I_B = 0$	2N6295, 2N6297			0.5	
Collector Cutoff Current		I _{CEX}			mAdc
V_{CE} = Rated V_{CB} , $V_{EB (off)}$ = 1.5 Vdc	2N6294, 2N6295	Ç.		0.5	
$V_{CE} = Rated V_{CB}, V_{BE (off)} = 1.5 Vdc$	2N6296, 2N6297			0.5	
V_{CE} = Rated V_{CB} , $V_{EB (off)}$ = 1.5 Vdc	2N6294, 2N6295			5.0	
$T_{\rm C} = 150^{\circ} {\rm C}$				5.0	
$V_{CE} = Rated V_{CB}, V_{BE (off)} = 1.5 Vdc$	2N6296, 2N6297			5.0	
$T_C = 150^{\circ}C$					
Emitter Cutoff Current		I _{EBO}			mAdc
$V_{BE} = 5.0 \text{ Vdc}, \ I_C = 0$				2.0	
ON CHARACTERISTICS (1)					
DC Current Gain		h _{FE}			
$I_{C} = 2.0 \text{ Adc}, V_{CE} = 3.0 \text{ Vdc}$			750	18000	
$I_{C} = 4.0 \text{ Adc}, V_{CE} = 3.0 \text{ Vdc}$			100		
Collector-Emitter Saturation Voltage		V _{CE(sat)}			Vdc
$I_C = 2.0 \text{ Adc}, I_B = 8.0 \text{ mAdc}$, , , , , , , , , , , , , , , , , , ,		2.0	
$I_{\rm C} = 4.0$ Adc, $I_{\rm B} = 40$ mAdc				3.0	
Base-Emitter Saturation Voltage		V _{BE(sat)}			Vdc
$I_{\rm C} = 4.0$ Adc, $I_{\rm B} = 40$ mAdc				4.0	
Base-Emitter On Voltage		V _{BE(on)}			Vdc
$I_{C} = 2.0 \text{ Adc}, V_{CE} = 3.0 \text{ Vdc}$				2.8	
DYNAMIC CHARACTERISTICS					
Magnitude of Common Emitter Small-Signal		h _{fe}			
Short-Circuit Forward Current Transfer Ratio					
$I_{\rm C} = 1.5 {\rm Adc}, V_{\rm CE} = 3.0 {\rm Vdc}, f = 1.0 {\rm Mhz}$			4.0		
Output Capacitance				1.00	pr
$V_{CB} = 10 \text{ Vdc}, I_E = 0, f = 0.1 \text{ Mhz}$	2N6294, 2N6295	C _{ob}		120	
	2N6296, 2N6297			200	
Small-Signal Current Gain		h _{fe}	300		
$I_C = 1.5 \text{ Adc}, V_{CE} = 3.0 \text{ Vdc}, f = 1.0 \text{ kHz}$			500		

*Indicates JEDEC registered data



T4-4.8-860-352 REV: --

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

Microchip: 2N6297 2N6296 2N6295